

### Surface mount diode

# Standard silicon rectifier diodes

#### S1A...S1M

**Forward Current: 1 A** 

Reverse Voltage: 50 to 1000 V

#### **Features**

- Max. solder temperature: 260°C
- Plastic material has UL classification 94V-0

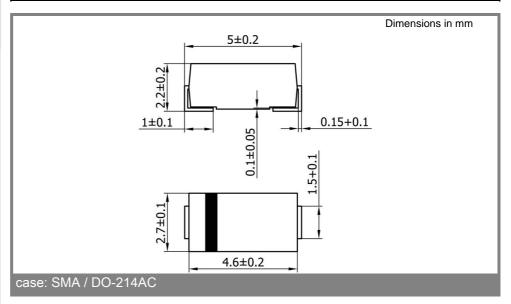
#### **Mechanical Data**

- Plastic case SMA / DO-214AC
- Weight approx.: 0,07 g
- Terminals: plated terminals solderable per MIL-STD-750
- Mounting position: any
- Standard packaging: 7500 pieces per reel
- 1) Max. temperature of the terminals  $T_T = 100 \, ^{\circ}C$
- 2) I<sub>F</sub> = 1 A, Tj = 25 °C
- 3)  $T_A = 25 \, ^{\circ}C$
- 4) Mounted on P.C. board with 25 mm<sup>2</sup> copper pads at each terminal

Туре	Polarity	Repetitive	Surge	Maximum	Maximum
	color	peak	peak	forward	reverse
	band	reverse	reverse	voltage	recovery
		voltage	voltage	T <sub>i</sub> = 25 °C	time
				I <sub>F</sub> = 1,0 A	I <sub>F</sub> = - A
					I <sub>R</sub> = - A
					I <sub>RR</sub> = - A
		$V_{RRM}$	$V_{RSM}$	$V_F^{2)}$	t <sub>rr</sub>
		V	V	V	ns
S1A	-	50	50	1,1	-
S1B	-	100	100	1,1	-
S1D	-	200	200	1,1	-
S1G	-	400	400	1,1	-
S1J	-	600	600	1,1	-
S1K	-	800	800	1,1	-
S1M	-	1000	1000	1,1	-

<b>Absolute Maximum Ratings</b> $T_c = 25  ^{\circ}\text{C}$ , unless otherwise specified						
Symbol	Conditions	Values	Units			
I <sub>FAV</sub>	Max. averaged fwd. current, R-load, T <sub>T</sub> = 100 °C	1	Α			
I <sub>FRM</sub>	Repetitive peak forward current f > 15 Hz <sup>1</sup> )	6	Α			
I <sub>FSM</sub>	Peak fwd. surge current 50 Hz half sinus-wave 3)	30	Α			
l²t	Rating for fusing, t < 10 ms <sup>3)</sup>	4,5	A²s			
R <sub>thA</sub>	Max. thermal resistance junction to ambient <sup>4</sup> )	70	K/W			
R <sub>thT</sub>	Max. thermal resistance junction to terminals	30	K/W			
T <sub>j</sub>	Operating junction temperature	- 50 + 150	°C			
T <sub>s</sub>	Storage temperature	- 50 <b>+</b> 150	°C			

Characte	ristics $T_c = 25  ^{\circ}\text{C},  \text{U}$	T <sub>c</sub> = 25 °C, unless otherwise specified		
Symbol	Conditions	Values	Units	
$I_R$	Maximum leakage current, $T_j = 25 \text{ °C}$ ; $V_R = V_{RRM}$	<5	μΑ	
	$T_j = 100 ^{\circ}\text{C};  V_R = V_{RRM}$	<50	μΑ	
CJ	Typical junction capacitance	-	pF	
	(at MHz and applied reverse voltage of V)			
$Q_{rr}$	Reverse recovery charge	-	μC	
	$(U_R = V; I_F = A; dI_F/dt = A/ms)$			
E <sub>RSM</sub>	Non repetitive peak reverse avalanche energy	-	mJ	
	$(I_R = mA; T_j = ^{\circ}C; inductive load switched off)$			



## S1A...S1M

